# **Octal Bus Buffer/Line Driver**

# **Inverting with 3-State Outputs**

The MC74VHCT240A is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT240A is an inverting 3-state buffer, and has two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT240A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage—input/output voltage mismatch, battery backup, hot insertion, etc.

#### **Features**

- High Speed:  $t_{PD} = 5.6 \text{ ns}$  (Typ) at  $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 1.1 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 110 FETs or 27.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

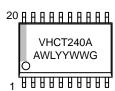


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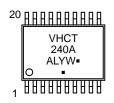
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#### MARKING DIAGRAMS









A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

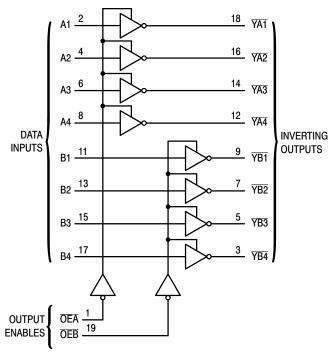


Figure 1. Logic Diagram

OEA [	1●	20	] v <sub>cc</sub>
A1 [	2	19	OEB
<u>YB4</u> [	3	18	YA1
A2 [	4	17	] B4
YB3 [	5	16	YA2
A3 [	6	15	] B3
YB2	7	14	YA3
A4 [	8	13	] B2
YB1 [	9	12	YA4
GND [	10	11	] B1

Figure 2. Pin Assignment

#### **FUNCTION TABLE**

INP	JTS	OUTPUTS
OEA, OEB A, B		YA, YB
L	L	Н
L	Н	L
Н	X	Z

#### **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage	- 0.5 to + 7.0	V	
V <sub>in</sub>	DC Input Voltage	- 0.5 to + 7.0	V	
V <sub>out</sub>	DC Output Voltage	- 0.5 to + 7.0 - 0.5 to V <sub>CC</sub> + 0.5	V	
I <sub>IK</sub>	Input Diode Current	<b>– 20</b>	mA	
I <sub>OK</sub>	Output Diode Current (V <sub>OUT</sub> < GNI	$V_{OUT} > V_{CC}$	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin		± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND	Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## RECOMMENDED OPERATING CONDITIONS

Symbol		Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		4.5	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage	Output in 3–State High or Low State	0 0	5.5 V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature		- 40	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> =5.0V ±0.5V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

<sup>†</sup>Derating – SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

#### DC ELECTRICAL CHARACTERISTICS

		V <sub>CC</sub> T <sub>A</sub> = 25°C		T <sub>A</sub> = - 40 to 85°C					
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V <sub>OH</sub>	Minimum High-Level Output	$I_{OH} = -50 \mu A$	4.5	4.4	4.5		4.4		V
	Voltage $V_{in} = V_{IH}$ or $V_{IL}$	I <sub>OH</sub> = - 8mA	4.5	3.94			3.80		-
V <sub>OL</sub>	Maximum Low-Level Output	I <sub>OL</sub> = 50μA	4.5		0.0	0.1		0.1	V
	Voltage $V_{in} = V_{IH}$ or $V_{IL}$	I <sub>OL</sub> = 8mA	4.5			0.36		0.44	-
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
I <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μА
Icc	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0	μА
Ісст	Quiescent Supply Current	Per Input: V <sub>IN</sub> = 3.4V Other Input: V <sub>CC</sub> or GND	5.5			1.35		1.50	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5V	0			0.5		5.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

				Т	A = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay A to YA or B to YB	$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.6 6.1	7.8 8.8	1.0 1.0	9.0 10.0	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time OEA to YA or OEB to YB	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.7 8.2	10.4 11.4	1.0 1.0	12.0 13.0	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time OEA to YA or OEB to YB	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C <sub>L</sub> = 50pF		8.8	11.4	1.0	13.0	ns
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 5.0 ± 0.5V (Note 1)	C <sub>L</sub> = 50pF			1.0		1.0	ns
C <sub>in</sub>	Maximum Input Capacitance				4	10		10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High–Impedance State)				9				pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_{PD}$	Power Dissipation Capacitance (Note 2)	19	pF

# **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0 \text{ns}$ , $C_L = 50 \text{pF}$ , $V_{CC} = 5.0 \text{V}$ )

		T <sub>A</sub> = 25°C		
Symbol	Parameter		Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.9	1.1	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.9	- 1.1	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per bit). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

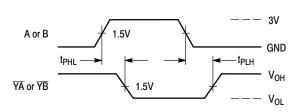


Figure 3. Switching Waveform

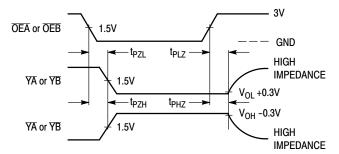
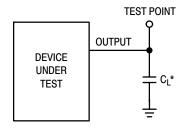
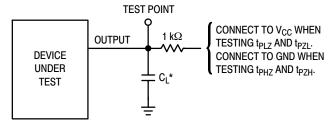


Figure 4. Switching Waveform



\*Includes all probe and jig capacitance

Figure 5. Test Circuit



\*Includes all probe and jig capacitance

Figure 6. Test Circuit

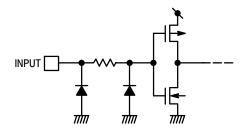


Figure 7. Input Equivalent Circuit

#### **ORDERING INFORMATION**

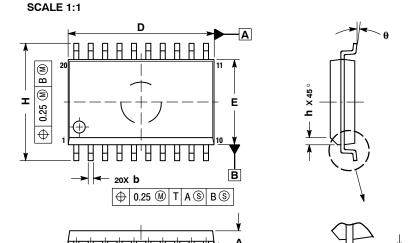
Device	Package	Shipping <sup>†</sup>
MC74VHCT240ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT240ADTRG	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SOIC-20 WB CASE 751D-05 **ISSUE H** 

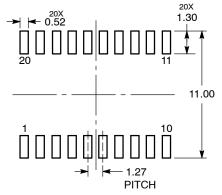
**DATE 22 APR 2015** 



- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

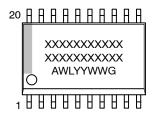
	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
b	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
A	0 °	7 °			

#### **RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

## **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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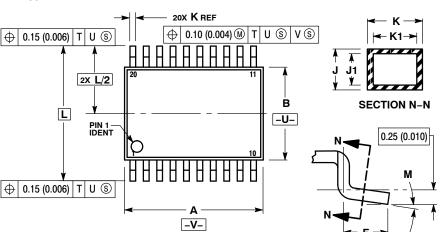
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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

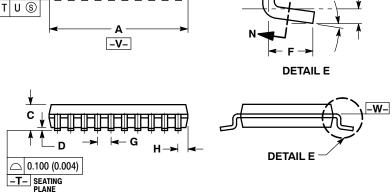


## TSSOP-20 WB CASE 948E ISSUE D

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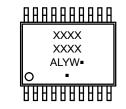
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
M	0°	8°	0°	8°

#### **GENERIC SOLDERING FOOTPRINT MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DIMENSIONS: MILLIMETERS

0.65

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16X

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